

NGTB40N120IHRWG

IGBT with Monolithic Free Wheeling Diode

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop (FS) Trench construction, and provides superior performance in demanding switching applications, offering both low on-state voltage and minimal switching loss. The IGBT is well suited for resonant or soft switching applications.

Features

- Extremely Efficient Trench with Fieldstop Technology
- Low Switching Loss Reduces System Power Dissipation
- Optimized for Low Losses in IH Cooker Application
- Reliable and Cost Effective Single Die Solution
- This is a Pb-Free Device

Typical Applications

- Inductive Heating
- Consumer Appliances
- Soft Switching

ABSOLUTE MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|-----------|----------------------|------------------|
| Collector-emitter voltage | V_{CES} | 1200 | V |
| Collector current @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$ | I_C | 80 40 | A |
| Pulsed collector current, T_{pulse} limited by T_{Jmax} , 10 μs pulse, $V_{GE} = 15\text{ V}$ | I_{CM} | 120 | A |
| Diode forward current @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$ | I_F | 80 40 | A |
| Diode pulsed current, T_{pulse} limited by T_{Jmax} , 10 μs pulse, $V_{GE} = 0\text{ V}$ | I_{FM} | 120 | A |
| Gate-emitter voltage Transient Gate-emitter voltage ($T_{pulse} = 5\ \mu\text{s}$, $D < 0.10$) | V_{GE} | ± 20 ± 25 | V |
| Power Dissipation @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$ | P_D | 384 192 | W |
| Operating junction temperature range | T_J | -40 to +175 | $^\circ\text{C}$ |
| Storage temperature range | T_{stg} | -55 to +175 | $^\circ\text{C}$ |
| Lead temperature for soldering, 1/8" from case for 5 seconds | T_{SLD} | 260 | $^\circ\text{C}$ |

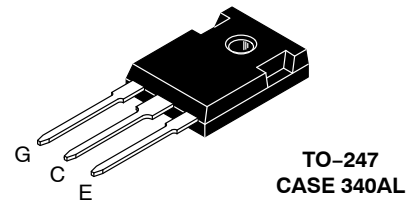
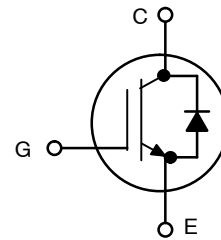
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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40 A, 1200 V
 $V_{CEsat} = 2.30\text{ V}$
 $E_{off} = 0.95\text{ mJ}$



MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

| Device | Package | Shipping |
|-----------------|---------------------|-----------------|
| NGTB40N120IHRWG | TO-247 (Pb-Free) | 30 Units / Rail |

NGTB40N120IHRWG

THERMAL CHARACTERISTICS

| Rating | Symbol | Value | Unit |
|--|-----------------|-------|-----------------------------|
| Thermal resistance junction-to-case | $R_{\theta JC}$ | 0.39 | $^{\circ}\text{C}/\text{W}$ |
| Thermal resistance junction-to-ambient | $R_{\theta JA}$ | 40 | $^{\circ}\text{C}/\text{W}$ |

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise specified)

| Parameter | Test Conditions | Symbol | Min | Typ | Max | Unit |
|-----------|-----------------|--------|-----|-----|-----|------|
|-----------|-----------------|--------|-----|-----|-----|------|

STATIC CHARACTERISTIC

| | | | | | | |
|---|---|---------------|------|--------------|------------|----|
| Collector-emitter breakdown voltage, gate-emitter short-circuited | $V_{GE} = 0\text{ V}, I_C = 500\ \mu\text{A}$ | $V_{(BR)CES}$ | 1200 | - | - | V |
| Collector-emitter saturation voltage | $V_{GE} = 15\text{ V}, I_C = 40\text{ A}$ $V_{GE} = 15\text{ V}, I_C = 40\text{ A}, T_J = 175^{\circ}\text{C}$ | V_{CEsat} | - | 2.30 2.70 | 2.55 - | V |
| Gate-emitter threshold voltage | $V_{GE} = V_{CE}, I_C = 250\ \mu\text{A}$ | $V_{GE(th)}$ | 4.5 | 5.5 | 6.5 | V |
| Collector-emitter cut-off current, gate-emitter short-circuited | $V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}$ $V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}, T_J = 175^{\circ}\text{C}$ | I_{CES} | - | - | 0.2 2.8 | mA |
| Gate leakage current, collector-emitter short-circuited | $V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$ | I_{GES} | - | - | 100 | nA |

DYNAMIC CHARACTERISTIC

| | | | | | | |
|------------------------------|--|-----------|---|------|---|----|
| Input capacitance | $V_{CE} = 20\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$ | C_{ies} | - | 5320 | - | pF |
| Output capacitance | | C_{oes} | - | 124 | - | |
| Reverse transfer capacitance | | C_{res} | - | 100 | - | |
| Gate charge total | $V_{CE} = 600\text{ V}, I_C = 40\text{ A}, V_{GE} = 15\text{ V}$ | Q_g | - | 225 | - | nC |
| Gate to emitter charge | | Q_{ge} | - | 36 | - | |
| Gate to collector charge | | Q_{gc} | - | 98 | - | |

SWITCHING CHARACTERISTIC, INDUCTIVE LOAD

| | | | | | | |
|-------------------------|--|--------------|---|------|---|----|
| Turn-off delay time | $T_J = 25^{\circ}\text{C}$ $V_{CC} = 600\text{ V}, I_C = 40\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$ | $t_{d(off)}$ | - | 230 | - | ns |
| Fall time | | t_f | - | 120 | - | |
| Turn-off switching loss | | E_{off} | - | 0.95 | - | |
| Turn-off delay time | $T_J = 150^{\circ}\text{C}$ $V_{CC} = 600\text{ V}, I_C = 40\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$ | $t_{d(off)}$ | - | 245 | - | ns |
| Fall time | | t_f | - | 180 | - | |
| Turn-off switching loss | | E_{off} | - | 2.10 | - | |

DIODE CHARACTERISTIC

| | | | | | | |
|-----------------|---|-------|---|--------------|-----------|---|
| Forward voltage | $V_{GE} = 0\text{ V}, I_F = 40\text{ A}$ $V_{GE} = 0\text{ V}, I_F = 40\text{ A}, T_J = 175^{\circ}\text{C}$ | V_F | - | 2.10 3.30 | 2.60 - | V |
|-----------------|---|-------|---|--------------|-----------|---|

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NGTB40N120IHRWG

TYPICAL CHARACTERISTICS

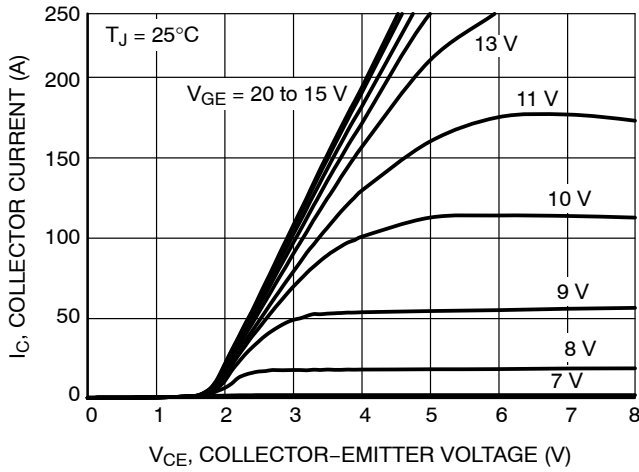


Figure 1. Output Characteristics

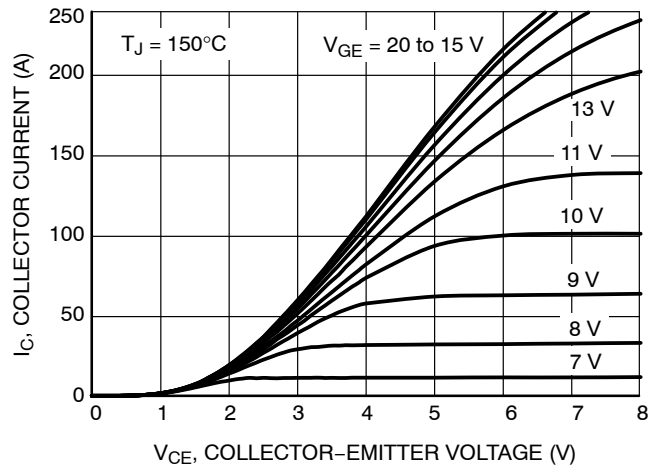


Figure 2. Output Characteristics

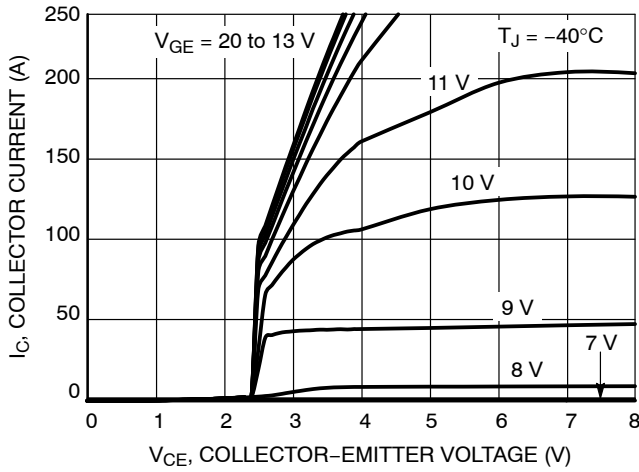


Figure 3. Output Characteristics

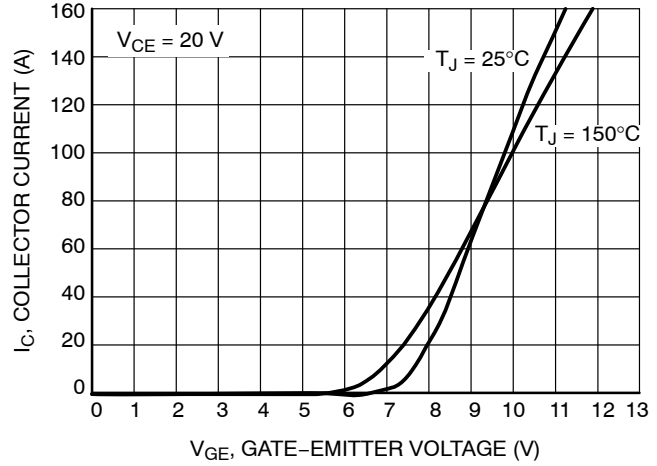


Figure 4. Typical Transfer Characteristics

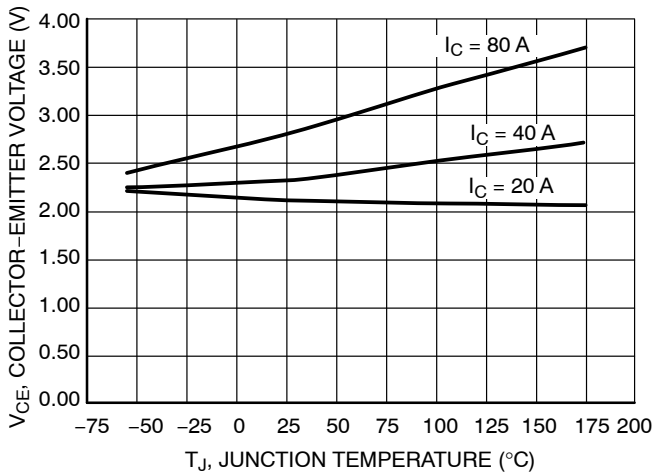


Figure 5. $V_{CE(sat)}$ vs. T_J

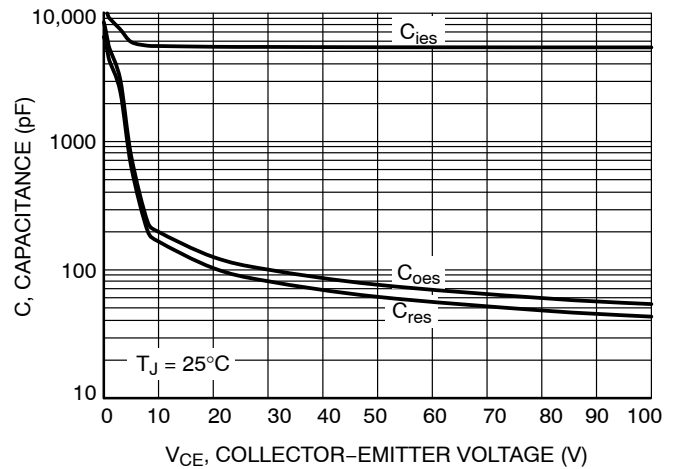


Figure 6. Typical Capacitance

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TYPICAL CHARACTERISTICS

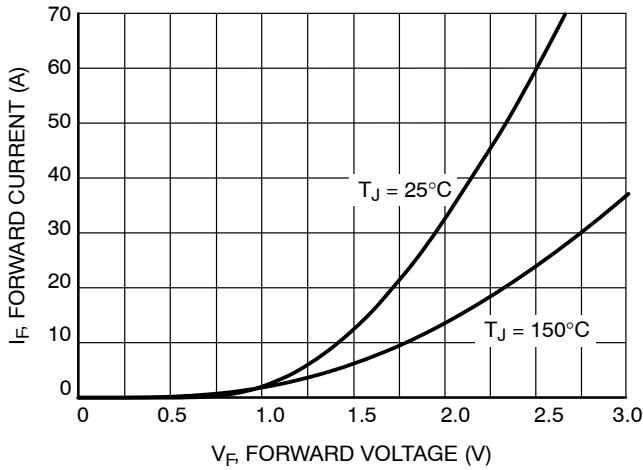


Figure 7. Diode Forward Characteristics

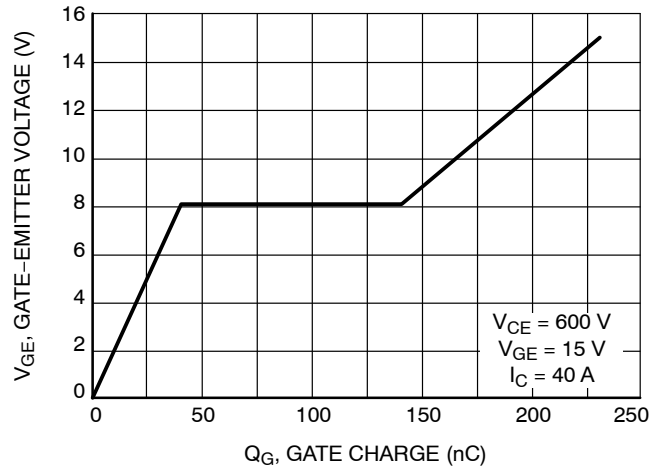


Figure 8. Typical Gate Charge

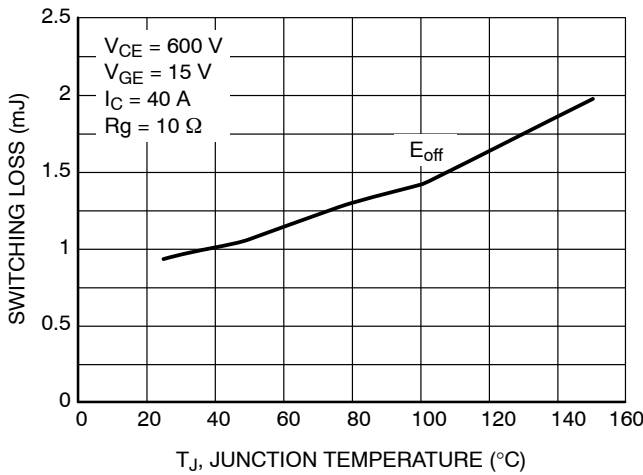


Figure 9. Switching Loss vs. Temperature

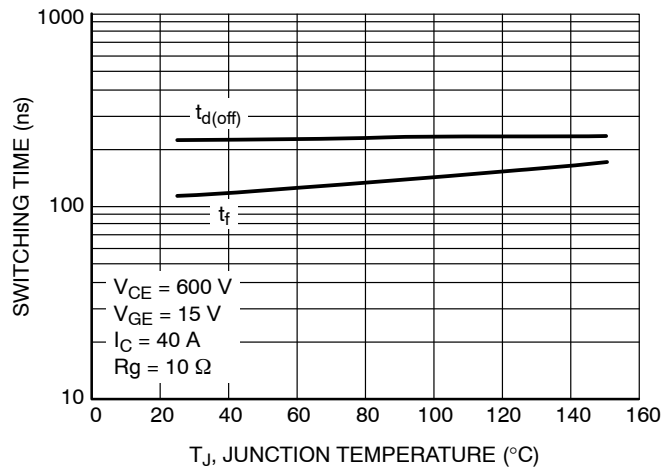


Figure 10. Switching Time vs. Temperature

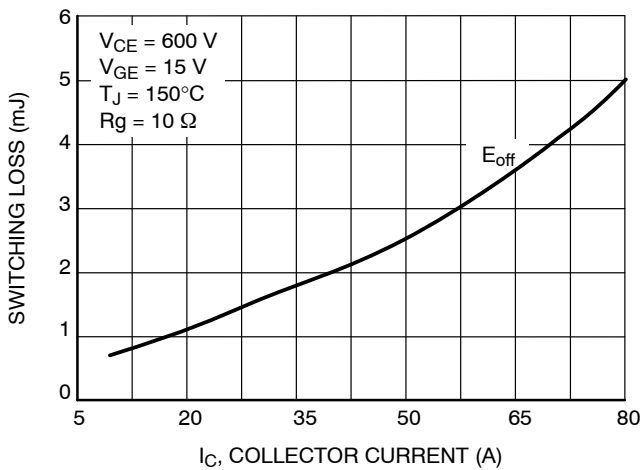


Figure 11. Switching Loss vs. I_C

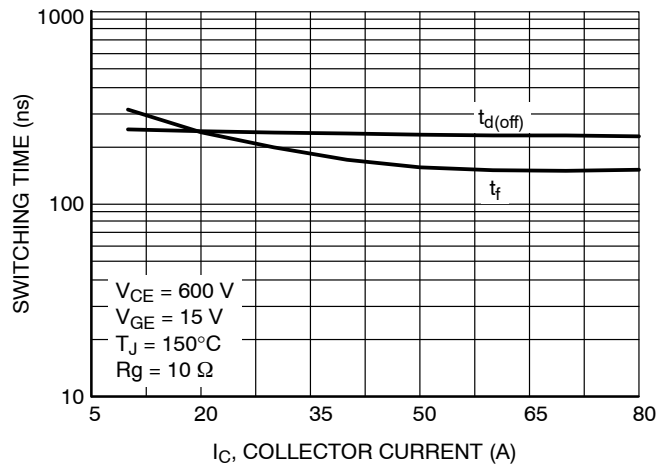


Figure 12. Switching Time vs. I_C

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TYPICAL CHARACTERISTICS

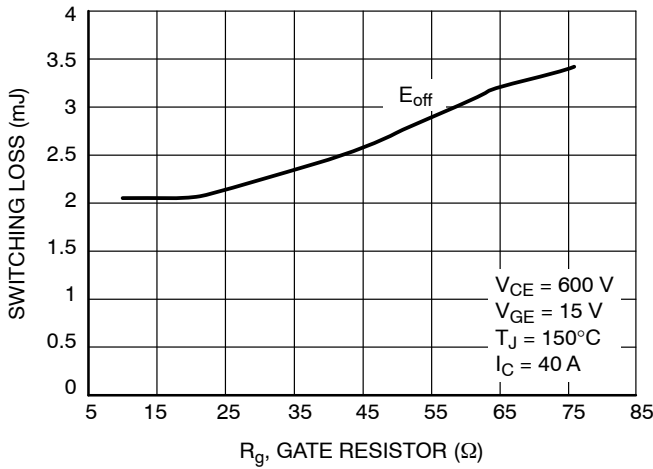


Figure 13. Switching Loss vs. R_g

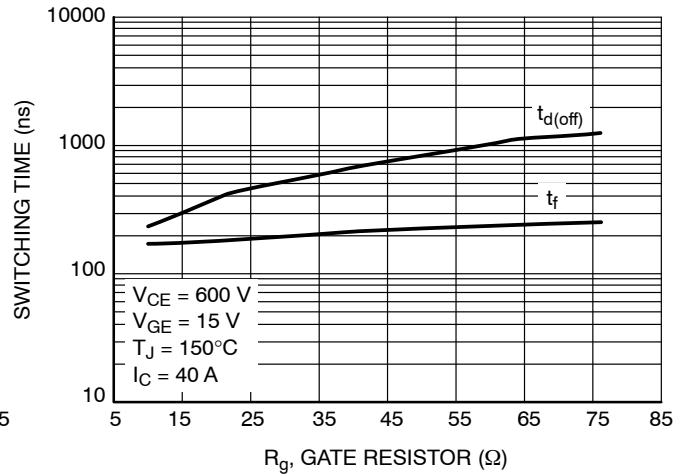


Figure 14. Switching Time vs. R_g

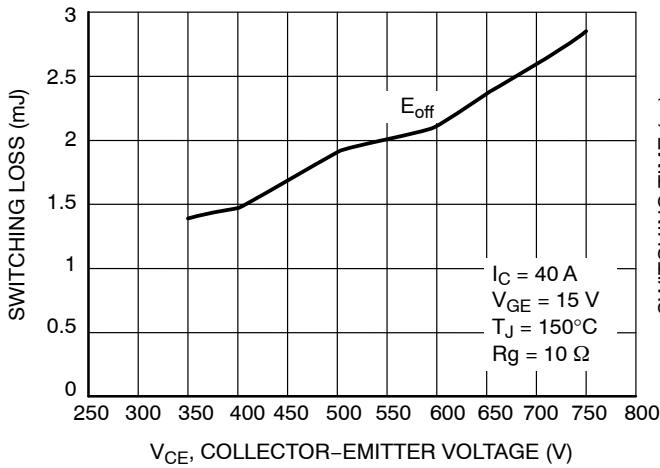


Figure 15. Switching Loss vs. V_{CE}

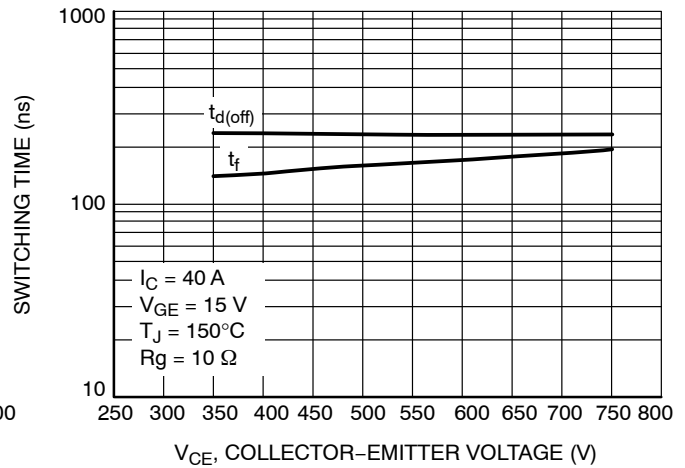


Figure 16. Switching Time vs. V_{CE}

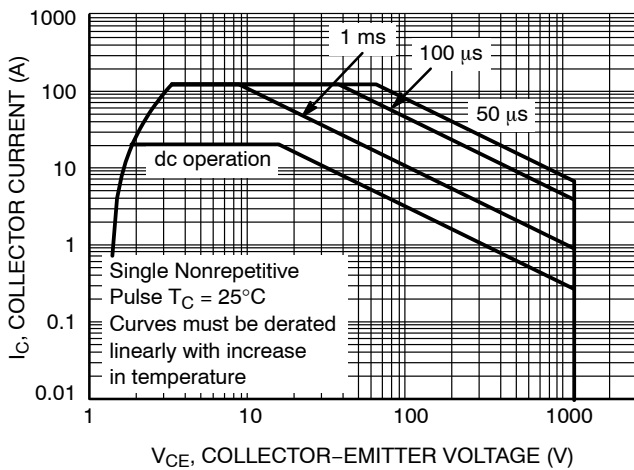


Figure 17. Safe Operating Area

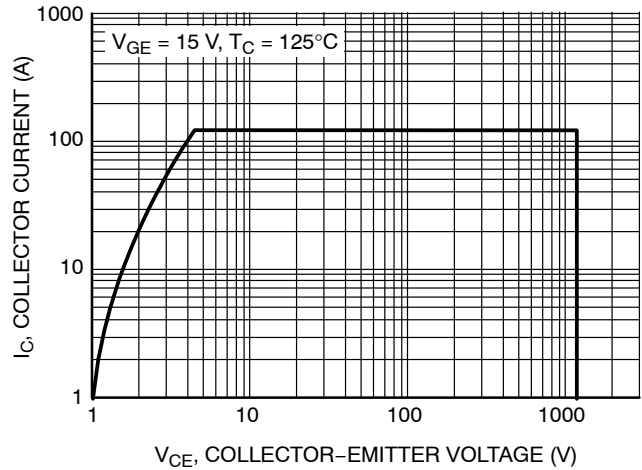


Figure 18. Reverse Bias Safe Operating Area

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TYPICAL CHARACTERISTICS

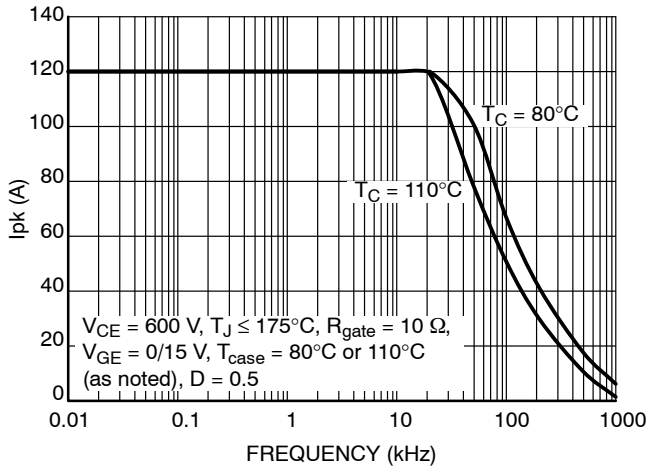


Figure 19. Collector Current vs. Switching Frequency

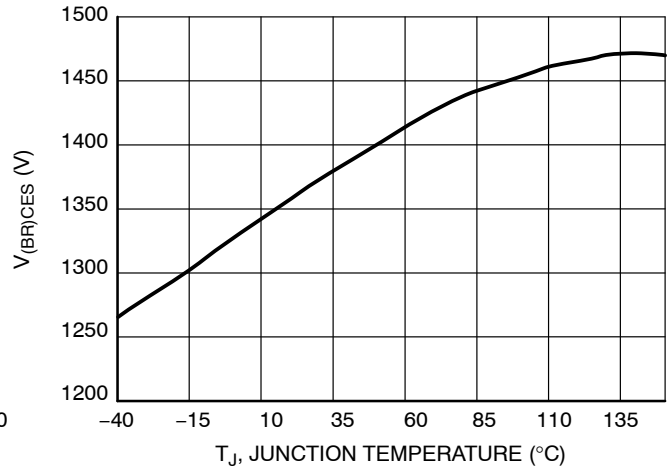


Figure 20. Typical $V_{(BR)CES}$ vs. Temperature

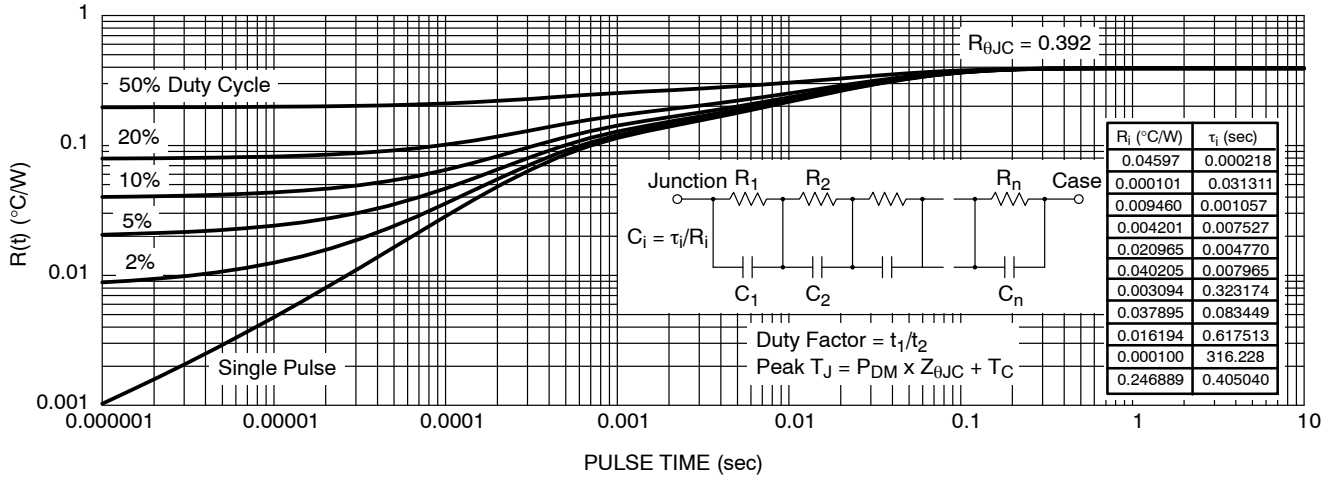


Figure 21. IGBT Transient Thermal Impedance

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Figure 22. Test Circuit for Switching Characteristics

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Figure 23. Definition of Turn On Waveform

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Figure 24. Definition of Turn Off Waveform

MECHANICAL CASE OUTLINE

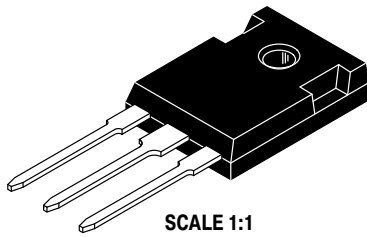
PACKAGE DIMENSIONS

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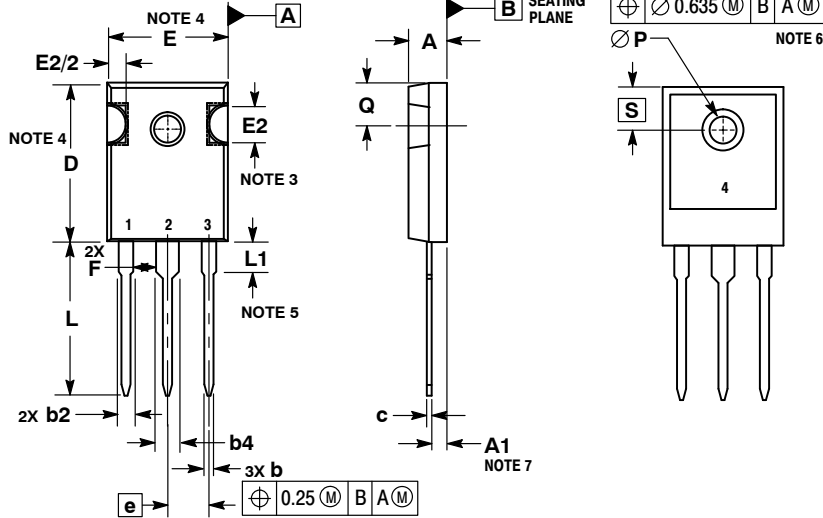


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CASE 340AL
ISSUE D

DATE 17 MAR 2017



SCALE 1:1

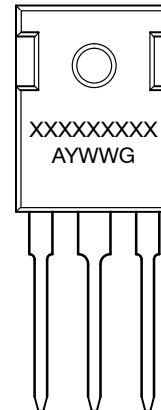


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. SLOT REQUIRED, NOTCH MAY BE ROUNDED.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
5. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.
6. ØP SHALL HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM DIAMETER OF 3.91.
7. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.

| MILLIMETERS | | |
|-------------|----------|-------|
| DIM | MIN | MAX |
| A | 4.70 | 5.30 |
| A1 | 2.20 | 2.60 |
| b | 1.07 | 1.33 |
| b2 | 1.65 | 2.35 |
| b4 | 2.60 | 3.40 |
| c | 0.45 | 0.68 |
| D | 20.80 | 21.34 |
| E | 15.50 | 16.25 |
| E2 | 4.32 | 5.49 |
| e | 5.45 BSC | |
| F | 2.655 | --- |
| L | 19.80 | 20.80 |
| L1 | 3.81 | 4.32 |
| P | 3.55 | 3.65 |
| Q | 5.40 | 6.20 |
| S | 6.15 BSC | |

GENERIC MARKING DIAGRAM*



- XXXXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "▪", may or may not be present.

| | | |
|------------------|-------------|--|
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